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Publication date: 2024

Document Version Publisher's PDF, also known as Version of record

Link back to DTU Orbit

Citation (APA):

Vajner, D. A., Wasiluk, M., Holewa, P., Ostój-Zięba, E., von Helversen, M., Sakanas, A., Huck, A., Yvind, K., Gregersen, N., Musial, A., Syperek, M., Semenova, E., & Heindel, T. (2024). *InAs(P)/InP QDs as sources of single indistinguishable photons at 1.55 µm*. Abstract from 12¹¹ International Conference on Quantum Dots, Munich, Bavaria, Germany.

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InAs(P)/InP QDs as sources of single indistinguishable photons at 1.55 µm

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Epitaxial quantum dots (QDs) exhibit substantial promise as non-classical light sources in quantum technologies [1]. In particular, the generation of single, indistinguishable photons on demand is pivotal for advanced quantum cryptographic key exchange algorithms [2]. This study investigates the quantum optical characteristics of single photons emitted by InAs(P)/InP QDs heterogeneously integrated with silicon.

The investigated QDs, grown via metalorganic vapor-phase epitaxy in the Stranski-Krastanow mode, showcase the emission at ~1.55 μ m [3], indispensable for long-haul, low-loss optical transmission through standard silica fibers. The photon extraction efficiency is enhanced to ~10% by employing a metallic mirror beneath the QDs in combination with a top mesa structure [4]. Our study confirms the single-photon emission from the QDs through measurements of the second-order autocorrelation function, revealing $g^{(2)}(0) = 0.005(4)$ for biexciton under two photon resonant excitation of the biexciton-exciton radiative cascade.

To investigate the degree of indistinguishability of emitted photons, we conducted also Hong-Ou-Mandel-type two-photon interference (TPI) experiment. The TPI visibility, quantifying the degree of indistinguishability of emitted photons, is crucial in examining the coherence of carriers within the QD [5]. Exciton-phonon interactions and carrier-carrier scattering significantly contribute to the degradation of coherence within the QDs. Using direct integration of the raw experimental data or fitting to a model, we evaluated the raw (i.e., 'as measured') and the post-selected TPI visibility up to 35% and 73%, respectively [6], which represents a state-of-the-art achievement for InAs/InP QDs emitting at 1.55 μ m. The significant progress in the generation of single indistinguishable photons in the telecom C-band offers crucial insights into their potential integration within quantum information technologies.

References

- [1] P. Michler, Quantum Dots for Quantum Information Technologies Vol. 237, Springer (2017).
- [2] D. A. Vajner *et al.*, *Quantum Communication Using Semiconductor Quantum Dots*, Adv. Quantum Technol. **5**, 2100116 (2022)
- [3] P. Holewa et al., Optical and electronic properties of low-density InAs/InP quantum-dot-like structures designed for single-photon emitters at telecom wavelengths, Phys. Rev. B 101, 195304 (2020).
- [4] P. Holewa et al., Bright Quantum Dot Single-Photon Emitters at Telecom Bands Heterogeneously Integrated on Si, ACS Photonics 9, 7, 2273–2279 (2022).
- [5] L. Wells et al., Coherent light scattering from a telecom C-band quantum dots, arXiv:2205.07997v2
- [6] D. Vajner et al., On-demand Generation of Indistinguishable Photons in the Telecom C-Band using Quantum Dot Devices, arXiv:2306.08668v1